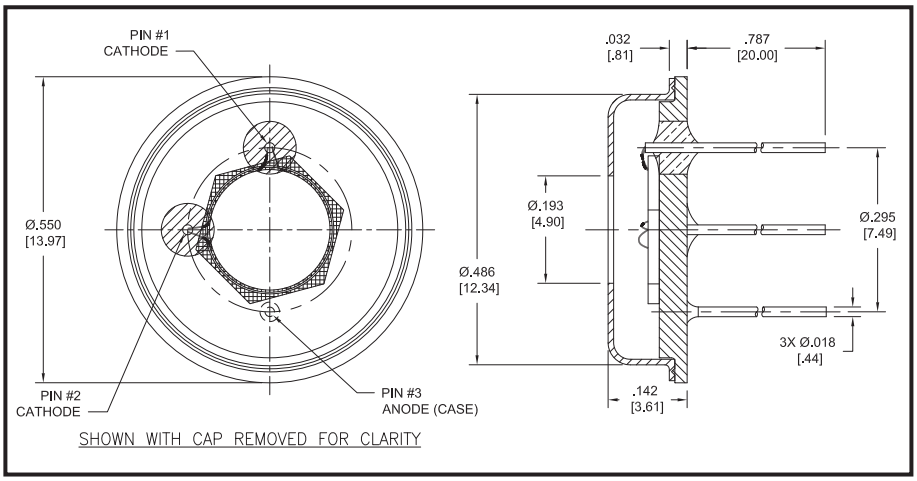


FEATURES

- Circular active area
- Ideal for electron detection
- 100% internal QE
- TO-8 package

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area[1]	Ø 4.9 mm		19		mm^2
Responsivity, $\mathcal{R}$	(see graph on next page)				A/W
Reverse Breakdown Voltage, V_R	I_R = 1 μA		9		Volts
Capacitance, C	V_R = 0 V		4	10	nF
Rise Time	RL = 50 Ω, V_R = 0 V	0.8	1.7	3.3	usec
Shunt Resistance	V_f = ± 10 mV	50	200		MOhms

[1]Die active area = Ø 5.5 mm, aperture size = Ø 4.9 mm

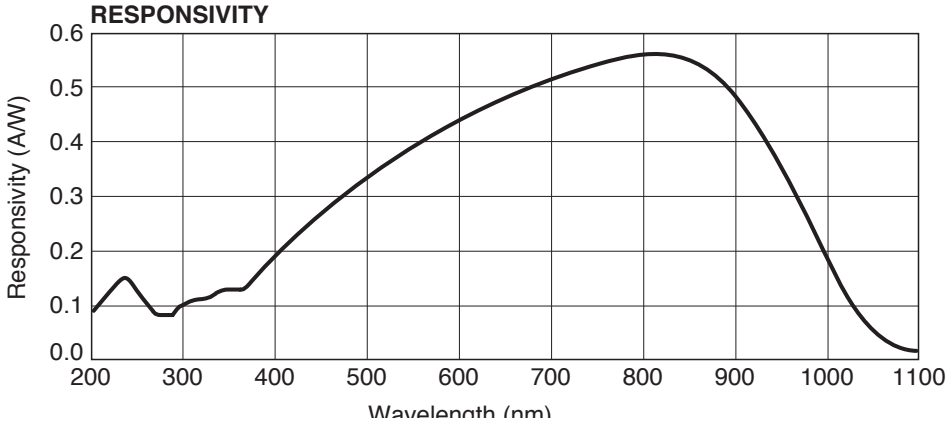
THERMAL PARAMETERS

Storage Temperature Range	-20° TO 100°C
Operating Temperature Range	-20°C TO 80°C
Maximum Junction Temperature	100°C
Lead Soldering Temperature[2]	240°C

[2]1/16" from case for 10 seconds

OPTO DIODE CORP.
750 Mitchell Road, Newbury Park, California 91320
Phone: (805) 499-0335, Fax: (805) 499-8108
Email: sales@optodiode.com, Website: www.optodiode.com

Revision April 18, 2013



OPTO DIODE CORP.
750 Mitchell Road, Newbury Park, California 91320
Phone: (805) 499-0335, Fax: (805) 499-8108
Email: sales@optodiode.com, Website: www.optodiode.com

Revision April 18, 2013